



Applications

Silicon Carbide implant annealing **Graphene by SiC sublimation RTCVD** of graphene High temperature annealing

The Zenith-150 high temperature rapid thermal processor can process samples up to 6-inch diameter at temperature up to 2000°C, one hour.

The system has a stainless steel water-cooled chamber. The cold wall chamber technology provides significant advantages: low memory effect, higher cooling rates.

The high temperature tungsten heaters provide enhanced temperature uniformity.

The pyrometer associated with the fast digital PID controller assure accurate and repeatable thermal control across the temperature range.

The design process chamber provides easy loading and unloading of the substrates and the installation of the thermocouple for calibration.

Human interface designed in respect of SEMI E95-0200

Full data logging and process historicals

Optional features

Control

Graphite and silicon carbide coated susceptors Soft-pumping valve Automatic pressure control with throttle valve

Customer support

Outstanding customer support for hardware, software and process Efficient remote support using software diagnostic capabilities High expertise in RTP processes of our process engineers Capability to support customer for process optimization

Physical specifications

Voltage: 3x400V+N+Gr / 3x220V+Gr

Power: 38 kW

Facilities Water: 2 to 4 bars, pressure drop 1 bar, 15 l/mn

Compressed air: 6 bars (valve actuation)

Process gas fittings: VCR 1/4

Dimensions ans weight
Width Depth Depth Depth Height Depth Height Depth Depth Depth Height Depth D







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